

**Features**

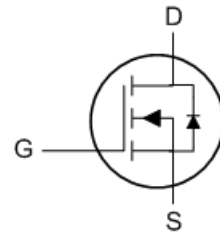
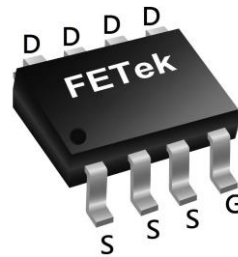
- ★ Advanced Trench MOS Technology
- ★ Low Gate Charge
- ★ 100% EAS Guaranteed
- ★ Green Device Available

**Applications**

- ★ Power Management Functions.
- ★ DC-DC Converters.
- ★ Backlighting.

**Product Summary**


BVDSS	RDSON	ID
40V	15mΩ	9.5A

**SOP8 Pin Configuration**

**Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	40	V
$V_{GS}$	Gate-Source Voltage	±20	V
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	9.5	A
$I_D@T_A=70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	7.5	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	40	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	14.5	mJ
$I_{AS}$	Avalanche Current	17	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation <sup>4</sup>	2.08	W
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$T_J$	Operating Junction Temperature Range	-55 to 150	°C

**Thermal Data**

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient (Steady State) <sup>1</sup>	---	60	°C/W
$R_{\theta JA}$	Thermal Resistance Junction-ambient ( $t \leq 10\text{sec}$ ) <sup>1</sup>	---	32	°C/W

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	40	---	---	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =6A	---	12.5	15	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A	---	19	23	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.2	1.7	2.4	V
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =32V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =32V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =12A	---	30	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	2.1	---	Ω
Q <sub>g</sub>	Total Gate Charge (4.5V)	V <sub>DS</sub> =32V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =6A	---	3.8	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	2.8	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	1.1	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =20V, V <sub>GS</sub> =10V, R <sub>G</sub> =3.3Ω I <sub>D</sub> =1A	---	12.2	---	ns
T <sub>r</sub>	Rise Time		---	5.3	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	18	---	
T <sub>f</sub>	Fall Time		---	9	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz	---	376	---	pF
C <sub>oss</sub>	Output Capacitance		---	240	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	19	---	

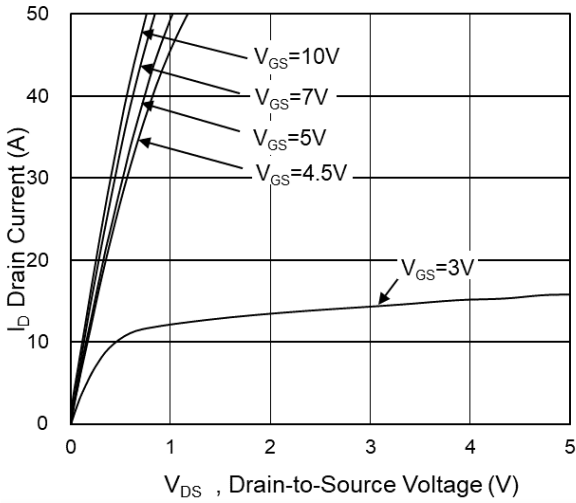
**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,5</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	3	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =6A, di/dt=100A/μs, T <sub>J</sub> =25°C	---	20	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge		---	35	---	nC

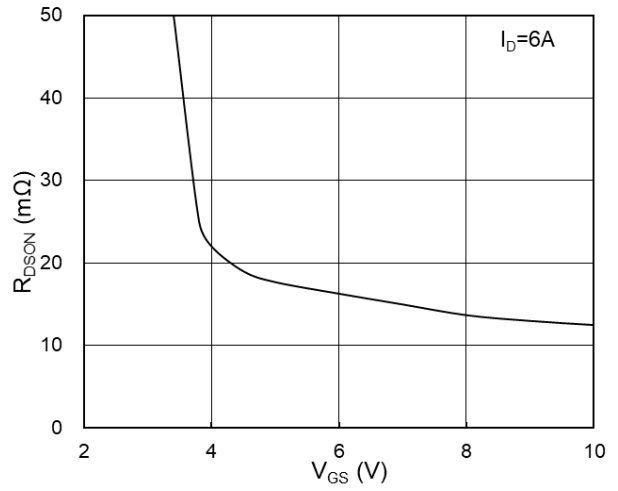
Note :

- The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 20Z copper.
- The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- The EAS data shows Max. rating. The test condition is V<sub>DD</sub>=25V, V<sub>GS</sub>=10V, L=0.1mH, I<sub>AS</sub>=17A
- The power dissipation is limited by 150°C junction temperature
- The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.

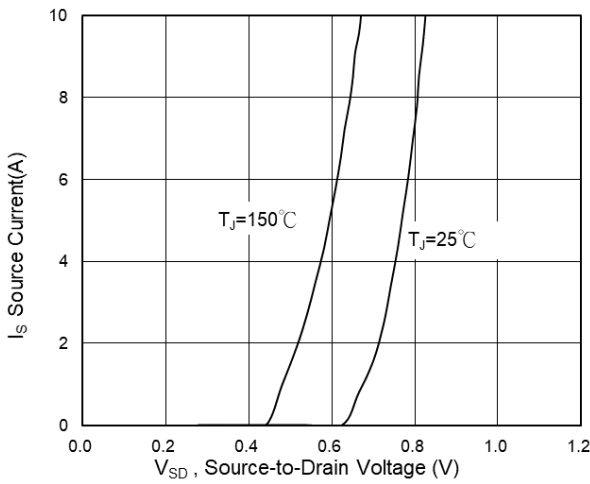
**Typical Characteristics**



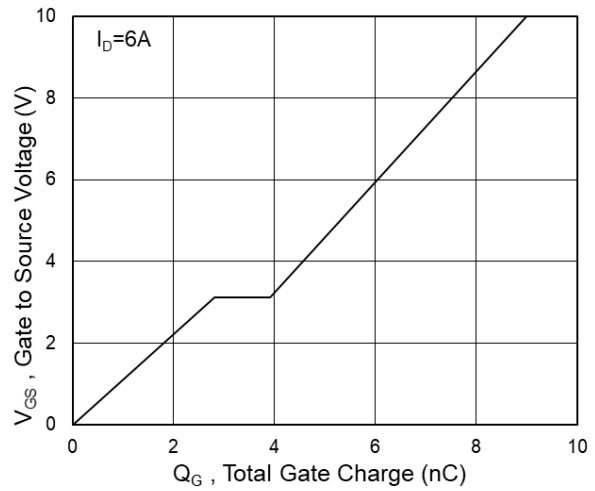
**Fig.1 Typical Output Characteristics**



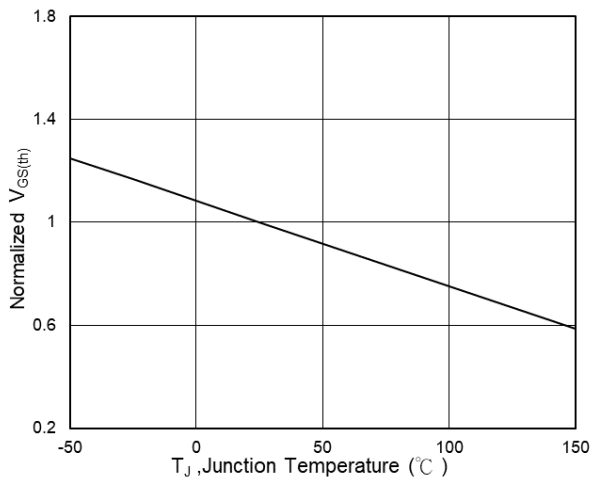
**Fig.2 On-Resistance vs G-S Voltage**



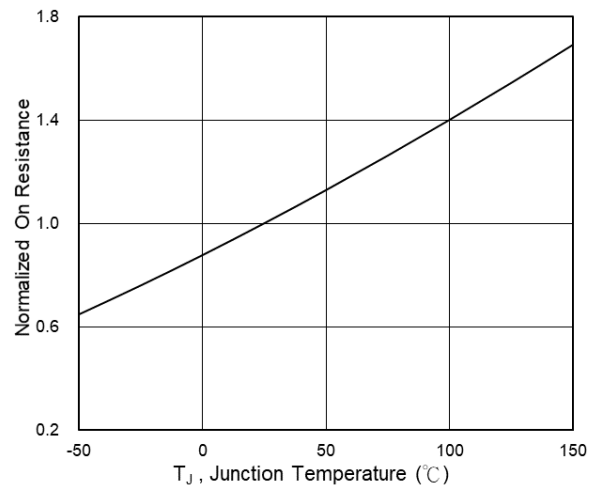
**Fig.3 Source Drain Forward Characteristics**



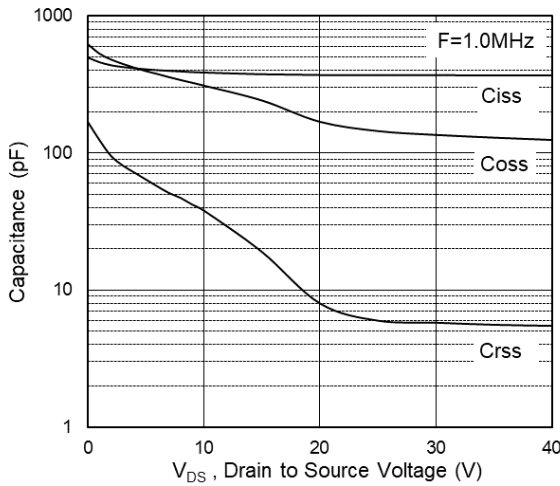
**Fig.4 Gate-Charge Characteristics**



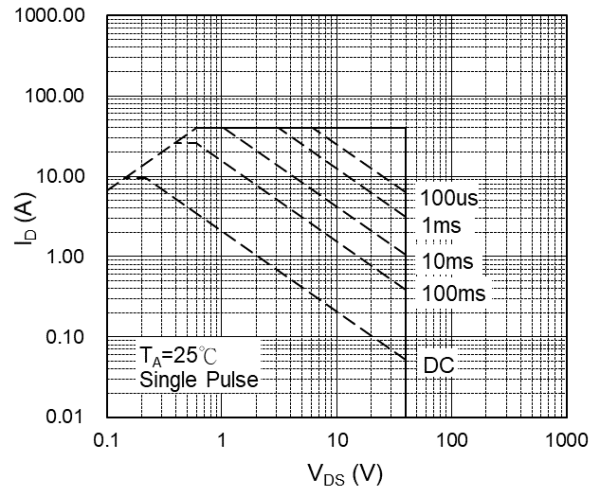
**Fig.5 Normalized  $V_{GS(th)}$  vs  $T_J$**



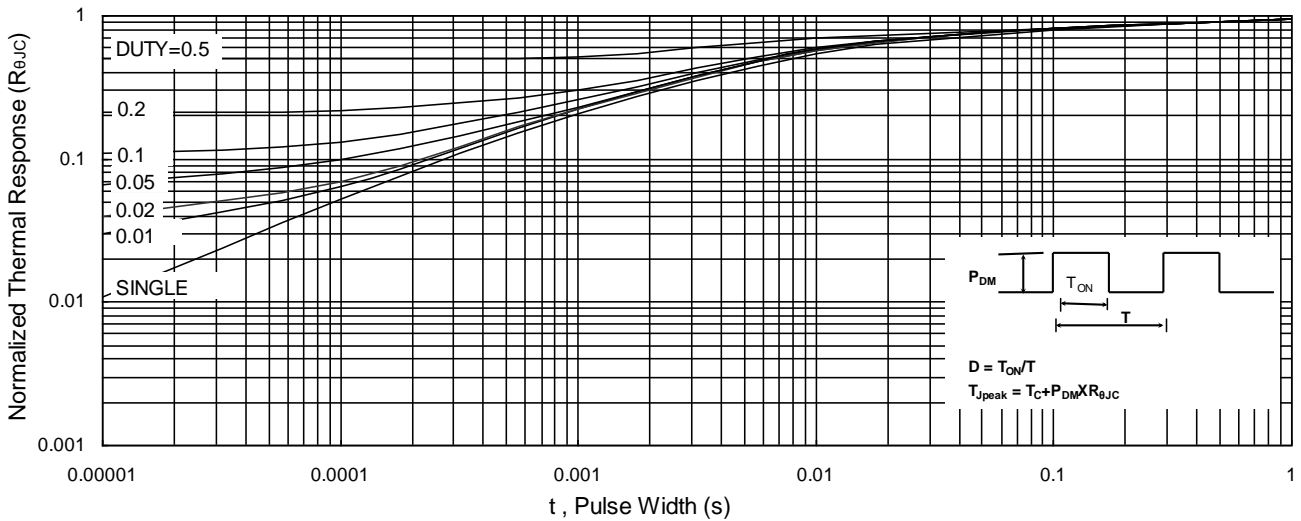
**Fig.6 Normalized  $R_{DS(on)}$  vs  $T_J$**



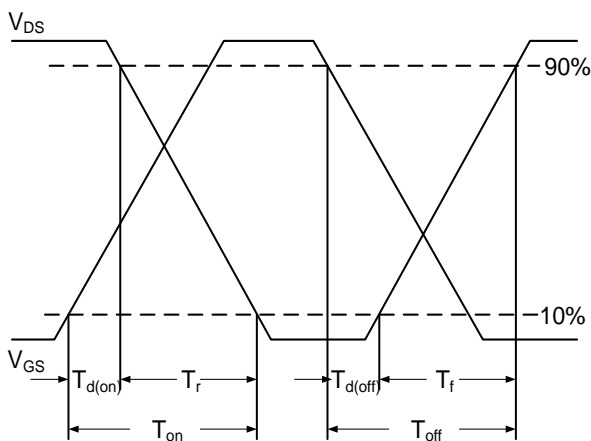
**Fig.7 Capacitance**



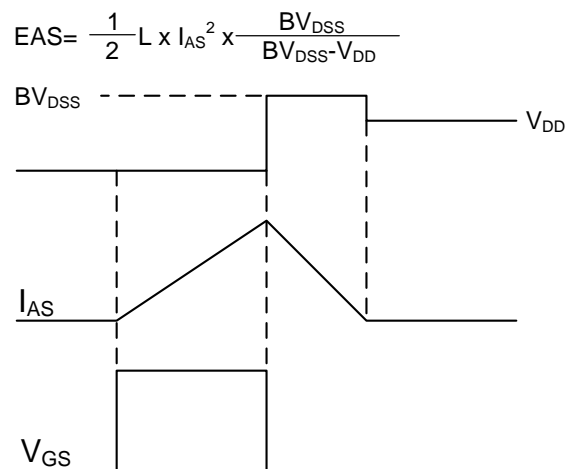
**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**



**Fig.10 Switching Time Waveform**



**Fig.11 Unclamped Inductive Switching Waveform**